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## 1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



**Product data sheet** 

## 1. General description

Ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

### 2. Features and benefits

- · Fast switching
- Guaranteed ESD capability
- High thermal cycling performance
- Low on-state loss
- Low thermal resistance
- Rugged: reverse voltage surge capability
- Soft recovery minimizes power-consuming oscillations

# 3. Applications

Output rectifiers in high-frequency switched-mode power supplies

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage			-	-	200	V
I <sub>F(AV)</sub>	average forward current	SQW; $\delta = 0.5$ ; $T_{mb} \le 128$ °C; <u>Fig. 1</u> ; <u>Fig. 2</u>		-	-	8	Α
Static characte	eristics						,
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>		-	0.8	0.895	V
Dynamic chara	acteristics						
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/s}$ ; $T_j = 25 \text{ °C}$ ; ramp recovery; Fig. 5; Fig. 7		-	20	25	ns
Electrostatic discharge							
V <sub>ESD</sub>	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ		-	-	8	kV





Ultrafast power diode

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode	}	001aaa020
mb	mb	mounting base; cathode	TO-220AC (SOD59)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package	ckage					
	Name	Description	Version				
BYW29E-200	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59				

# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	200	V
$V_{RWM}$	crest working reverse voltage		-	200	V
$V_R$	reverse voltage		-	200	V
I <sub>F(AV)</sub>	average forward current	SQW; δ = 0.5 ; T <sub>mb</sub> ≤ 128 °C; <u>Fig. 1</u> ; <u>Fig. 2</u>	-	8	Α
I <sub>FRM</sub>	repetitive peak forward current	SQW; $\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; $T_{mb} \le$ 128 °C	-	16	Α
I <sub>FSM</sub>	non-repetitive peak forward	SIN; $t_p = 8.3 \text{ ms}$ ; $T_{j(init)} = 25 \text{ °C}$	-	88	Α
	current	SIN; $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C	-	80	Α
I <sub>RRM</sub>	repetitive peak reverse current	$\delta = 0.001$ ; $t_p = 2 \mu s$	-	0.2	Α
I <sub>RSM</sub>	non-repetitive peak reverse current	t <sub>p</sub> = 100 μs	-	0.2	Α
T <sub>stg</sub>	storage temperature		-40	150	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>j</sub>	junction temperature			-	150	°C
Electrostatic discharge						
V <sub>ESD</sub>	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ		-	8	kV

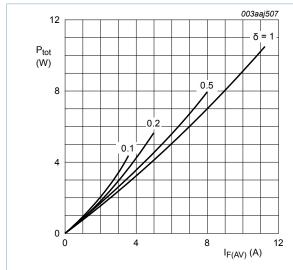


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_{O} &= 0.791 \text{ V; } R_{S} = 0.013 \text{ } \Omega \end{split}$$

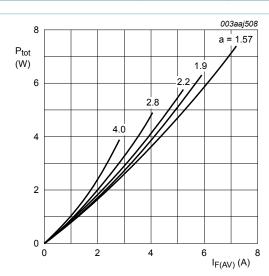


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

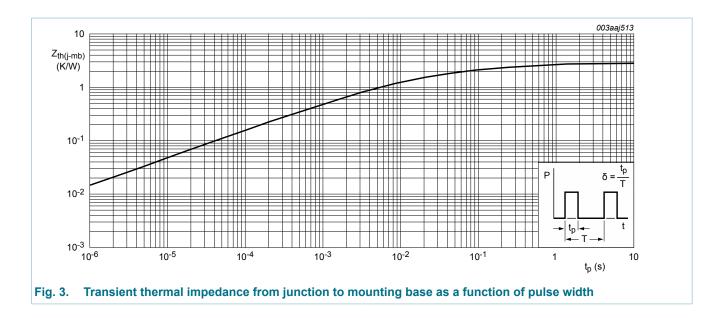
$$\begin{aligned} \mathbf{a} &= \mathbf{form} \ \mathbf{factor} = I_{F(RMS)} / I_{F(AV)} \\ \mathbf{V_O} &= \mathbf{0.791} \ \mathbf{V; R_S} = \mathbf{0.013} \ \Omega \end{aligned}$$

## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 3	-	-	2.7	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W

### Ultrafast power diode

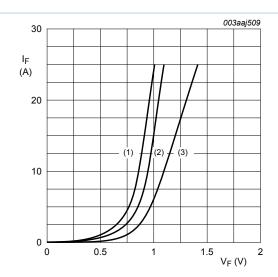


## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics				'	
$V_{F}$	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>	-	0.92	1.05	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>	-	1.1	1.3	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>	-	0.8	0.895	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 200 V; T <sub>j</sub> = 25 °C	-	2	10	μΑ
		V <sub>R</sub> = 200 V; T <sub>j</sub> = 100 °C	-	0.2	0.6	mA
Dynamic cl	haracteristics					
Q <sub>r</sub>	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A/s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 5; Fig. 6$	-	4	11	nC
t <sub>rr</sub>	reverse recovery time	$I_F$ = 1 A; $V_R$ = 30 V; $dI_F/dt$ = 100 A/s; $T_j$ = 25 °C; ramp recovery; <u>Fig. 5</u> ; <u>Fig. 7</u>	-	20	25	ns
		$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{R(meas)} = 0.25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ step recovery}; Fig. 8$	-	15	20	ns
$V_{FRM}$	forward recovery voltage	$I_F = 1 \text{ A}; dI_F/dt = 10 \text{ A/s}; T_j = 25 °C;$ Fig. 9	-	1	-	V

#### **Ultrafast power diode**





(1)  $T_i = 150$  °C; typical values;

(2) T<sub>i</sub> = 150 °C; maximum values;

(3)  $T_i = 25$  °C; maximum values;

 $V_O = 0.791 \text{ V}; R_S = 0.013 \Omega$ 

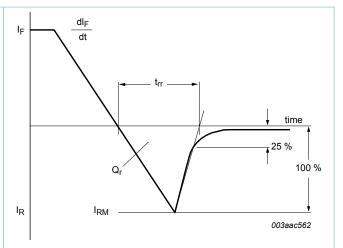


Fig. 5. Reverse recovery definitions; ramp recovery

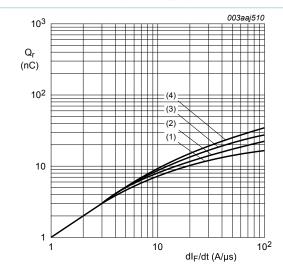


Fig. 6. Recovered charge as a function of rate of change of forward current; maximum values

(1) 
$$I_F = 1 A$$
;  $T_i = 25 \, ^{\circ}\text{C}$ 

(2) 
$$I_F = 2 A$$
;  $T_j = 25 \, ^{\circ}\mathrm{C}$ 

(3) 
$$I_F = 5 A$$
;  $T_j = 25 \, ^{\circ}\text{C}$ 

(4) 
$$I_F = 10 A; T_i = 25 °C$$

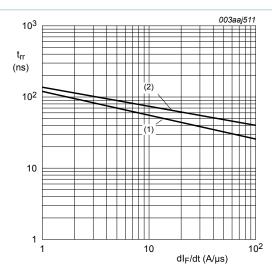
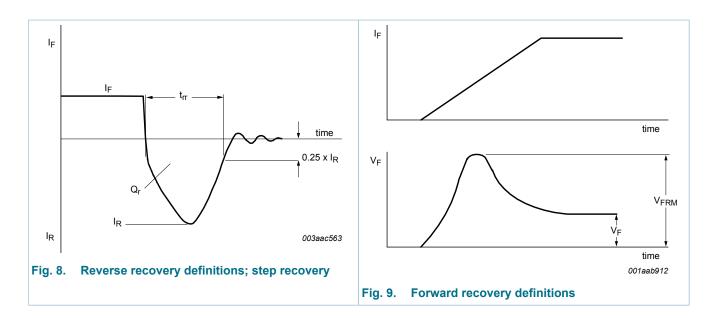


Fig. 7. Reverse recovery time as a function of rate of change of forward current; maximum values

(1) 
$$I_F = 1 A$$
;  $T_i = 25 \, ^{\circ}C$ 

(2) 
$$I_F = 10 \text{ A}; T_j = 25 \text{ }^{\circ}\text{C}$$

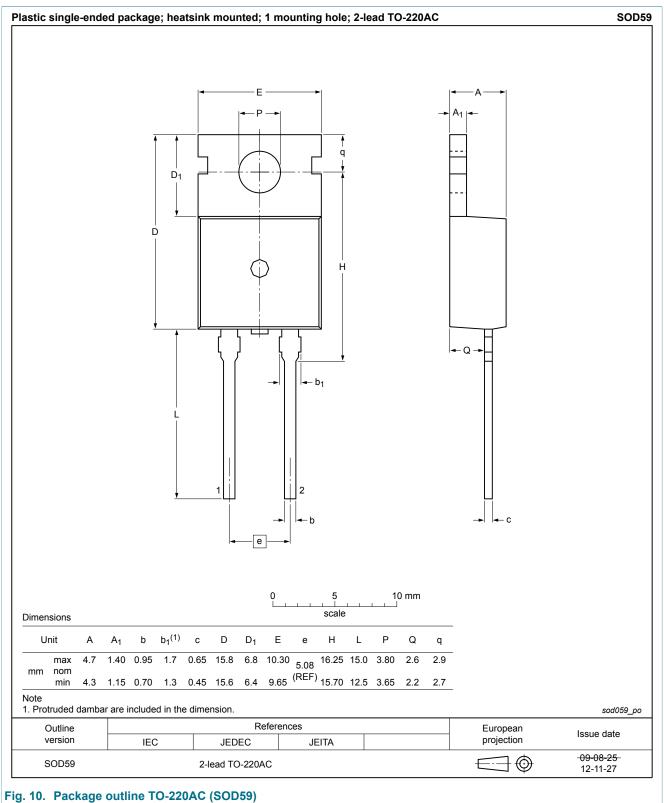
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## 10. Package outline



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#### Ultrafast power diode

## 11. Legal information

#### 11.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- Please consult the most recently issued document before initiating or completing a design.
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